MJE13003D-P

Preliminary

NPN SILICON TRANSISTOR

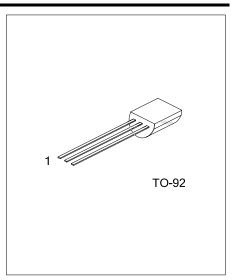
HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

■ DESCRIPTION

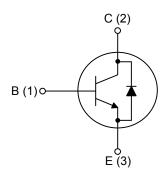
The UTC **MJE13003D-P** is a NPN Power Transistor. It is intended to be used in applications requiring medium voltage capability and high switching speeds.

■ FEATURES

- * Fast-Switching And High Voltage Capability
- * Dynamic Parameters With Low Spread
- * High Reliability
- * Integrated Antiparallel Collector-Emitter Diode



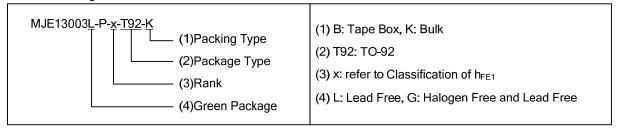
■ INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

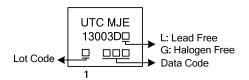
Ordering	Dookogo	Pin Assignment			Doolsing		
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13003DL-P-x-T92-B	MJE13003DG-P-x-T92-B	TO-92	E	С	В	Tape Box	
MJE13003DL-P-x-T92-K	MJE13003DG-P-x-T92-K	TO-92	E	С	В	Bulk	

Note: Pin Assignment: C: Collector B: Base E: Emitter



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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector- Emitter Voltage (V _{BE} =0)	V_{CES}	700	V
Collector-Emitter Voltage (I _B =0)	V_{CEO}	400	V
Emitter-Base Voltage (I_C =0, I_B =0.75A, t_P <10 μ S)	V_{EBO}	9	V
Collector Current	Ic	1.5	Α
Collector Peak Current (t _P <5ms)	I _{CM}	3	Α
Base Current	I _B	0.75	Α
Base Peak Current (t _P <5ms)	I _{BM}	1.5	Α
T _A =25°C	0	1.1	W
Power Dissipation $T_C=25^{\circ}C$	P _D	1.5	W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Emitter-Base Breakdown Voltage		BV_{EBO}	I _E =10mA, I _C =0	9		18	V
Collector-Emitter Sustaining Voltage (Note)		$V_{CEO(SUS)}$	I _C =10mA, I _B =0	450			V
Collector Cut-Off Current		I _{CES}	V _{CE} =700V,V _{BE} =0			1	mA
			I _C =0.5 A, I _B =0.1 A			0.5	V
Collector-Emitter Saturation	on Voltage (Note)	- (- /	I _C =1 A, I _B =0.25 A			1	V
			I _C =1.5 A, I _B =0.5 A			3	V
Base-Emitter Saturation Voltage (Note)		V _{BE(SAT)}	I _C =0.5 A, I _B =0.1 A			1	V
			I _C =1 A, I _B =0.25 A			1.2	V
DC Current Gain		h _{FE1}	I _C =0.4A, V _{CE} =5 V	14		57	
		h _{FE2}	I _C =1 A, V _{CE} =5 V	5		30	
Resistive Load	Rise Time	t_R	V _{CC} =125 V, I _C =1 A,			1	μs
	Storage Time	ts	I _{B1} =0.2 A, I _{B2} =-0.2 A			4	μs
	Fall Time	t_{F}	t _P =25µs			0.7	μs
Inductive Load Storage Time		ĪΩ	I _C =1 A, I _{B1} =0.2 A,V _{BE} =-5 V,		0.0		
			L=50mH, V _{CLAMP} =300V		8.0		μs
Diode Forward Voltage		V_{F}	I _F =0.5 A			1.5	V

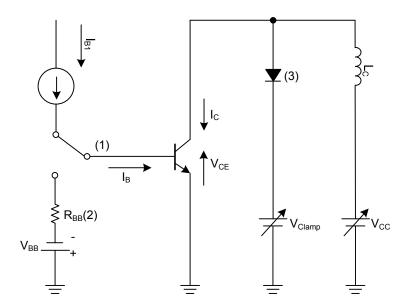
Note: Pulse Test: Pulse duration≤300µs, Duty cycle≤2 %

■ CLASSIFICATION OF h_{FE1}

RANK	Α	В	С	D	E	F	G	Н
RANGE	14 ~ 22	21 ~ 27	26 ~ 32	31 ~ 37	36 ~ 42	41 ~ 47	46 ~ 52	51 ~ 57

TEST CIRCURTS

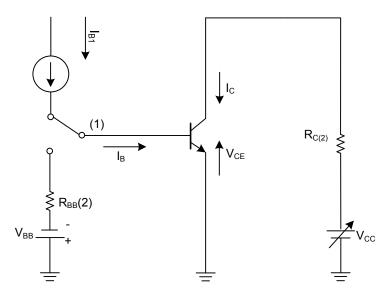
Inductive Load Switching Test Circuit



Notes: 1. Fast Electronic Switch

- 2. Non-Inductive Resistor
- 3. Fast Recovery Rectifier

Resistive Load Switching Test Circuit



- Notes: 1. Fast Electronic Switch
 - 2. Non-Inductive Resistor

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